

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}		K/W
BCR192		≤ 240	
BCR192W		≤ 105	

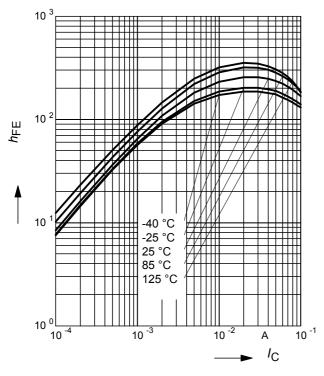
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V _{(BR)CEO}	50	-	-	V
$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm B} = 0$					
Collector-base breakdown voltage	V _{(BR)CBO}	50	-	-	
<i>I</i> _C = 10 μA, <i>I</i> _E = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB}$ = 40 V, $I_{\rm E}$ = 0					
Emitter-base cutoff current	I _{EBO}	-	-	227	μA
V _{EB} = 10 V, <i>I</i> _C = 0					
DC current gain ²⁾	h _{FE}	70	-	-	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 5 V					
Collector-emitter saturation voltage ²⁾	V _{CEsat}	-	-	0.3	V
<i>I</i> _C = 10 mA, <i>I</i> _B = 0,5 mA					
Input off voltage	V _{i(off)}	0.5	-	1.2	
$I_{\rm C}$ = 100 µA, $V_{\rm CE}$ = 5 V					
Input on voltage	V _{i(on)}	0.8	-	2.5	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0,3 V					
Input resistor	R ₁	15	22	29	kΩ
Resistor ratio	R ₁ /R ₂	0.42	0.47	0.52	-
AC Characteristics					
Transition frequency	f _T	-	200	-	MHz
<i>I</i> _C = 10 mA, <i>V</i> _{CE} = 5 V, <i>f</i> = 100 MHz					
Collector-base capacitance	C _{cb}	-	3	-	pF
$V_{\rm CB}$ = 10 V, <i>f</i> = 1 MHz					

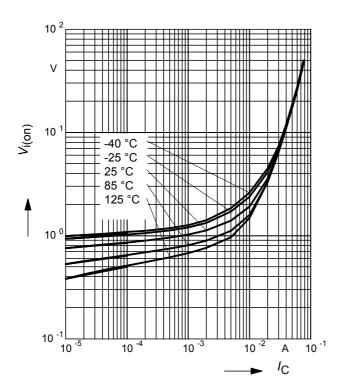
¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation) ²Pulse test: t < 300µs; D < 2%



DC current gain $h_{FE} = f(I_C)$ $V_{CE} = 5 V$ (common emitter configuration)

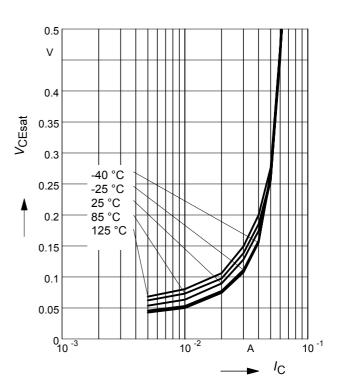


Input on Voltage $V_{i(on)} = f(I_C)$ $V_{CE} = 0.3V$ (common emitter configuration)

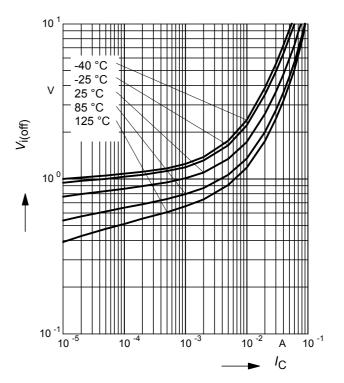


Collector-emitter saturation voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), I_{\text{C}}/I_{\text{B}} = 20$

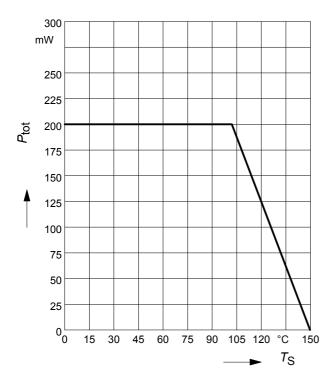


Input off voltage $V_{i(off)} = f(I_C)$ $V_{CE} = 5V$ (common emitter configuration)

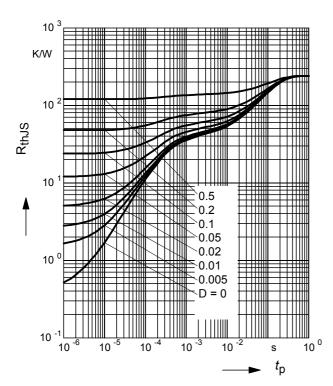




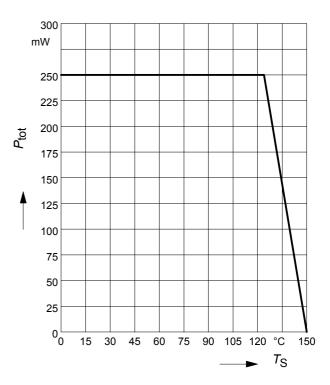
Total power dissipation $P_{tot} = f(T_S)$ BCR192



Permissible Pulse Load $R_{thJS} = f(t_p)$ BCR192

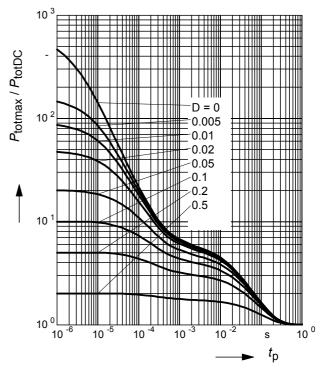


Total power dissipation $P_{tot} = f(T_S)$ BCR192W



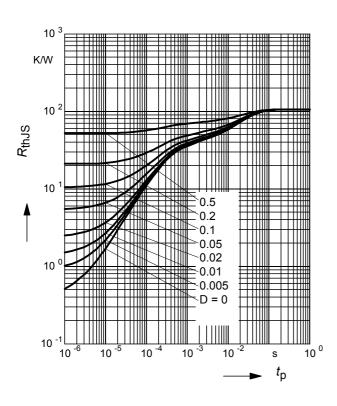
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$ BCR192



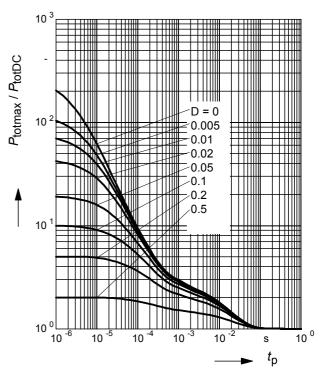


Permissible Puls Load $R_{\text{thJS}} = f(t_{\text{p}})$ BCR192W

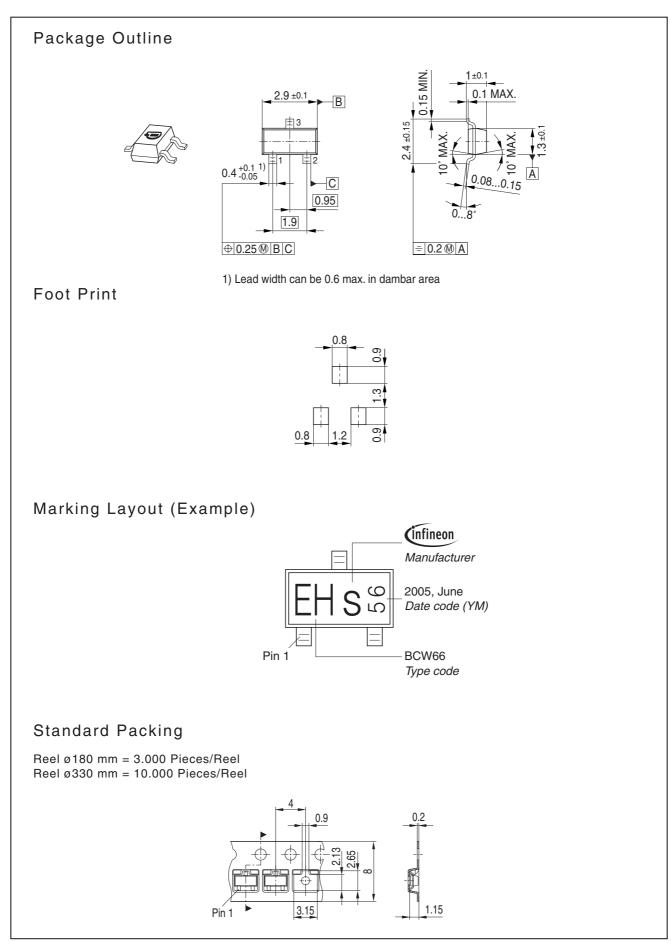


Permissible Pulse Load

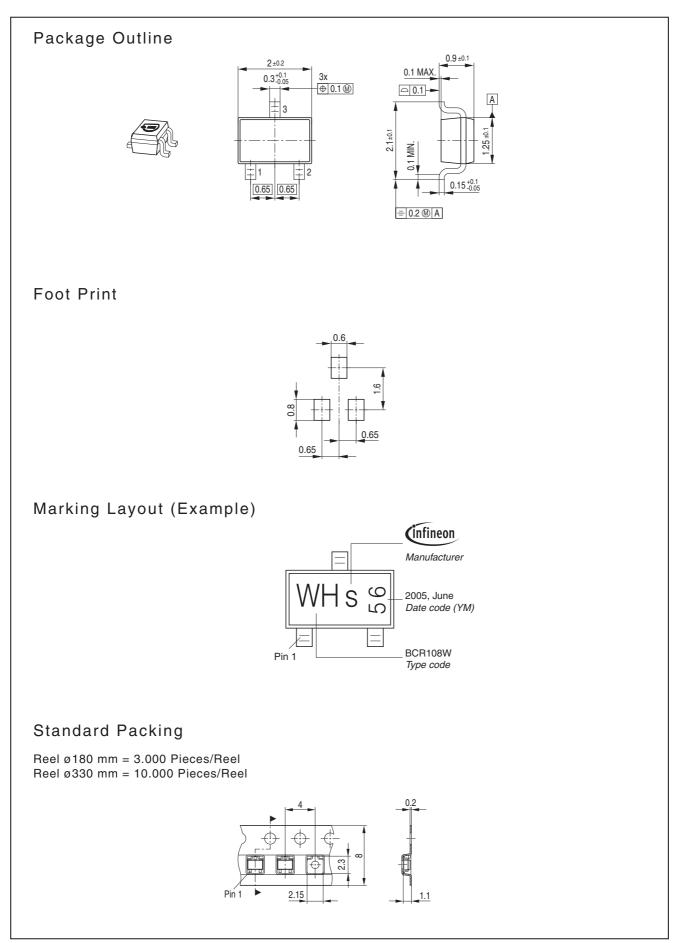
















Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

© 2009 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (<<u>www.infineon.com</u>>).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.